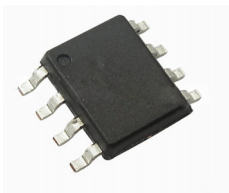
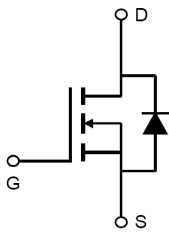


SOP-8      N      MOS      N-Channel MOSFET in a SOP-8 Plastic Package.

$R_{DS\ ON}$       RoHS  
 Low  $R_{DS(ON)}$ , Low Gate Charge, Optimized for fast-switching, RoHS .

DC/DC    AC/DC      /  
 Synchronous Rectification in DC/DC and AC/DC Converters, Isolated DC/DC Converters in Telecom and Industrial.



PIN1:S      PIN 2:S      PIN 3   S      PIN 4   G  
 PIN5   PIN 6   PIN 7   PIN 8:D

See Marking Instructions.

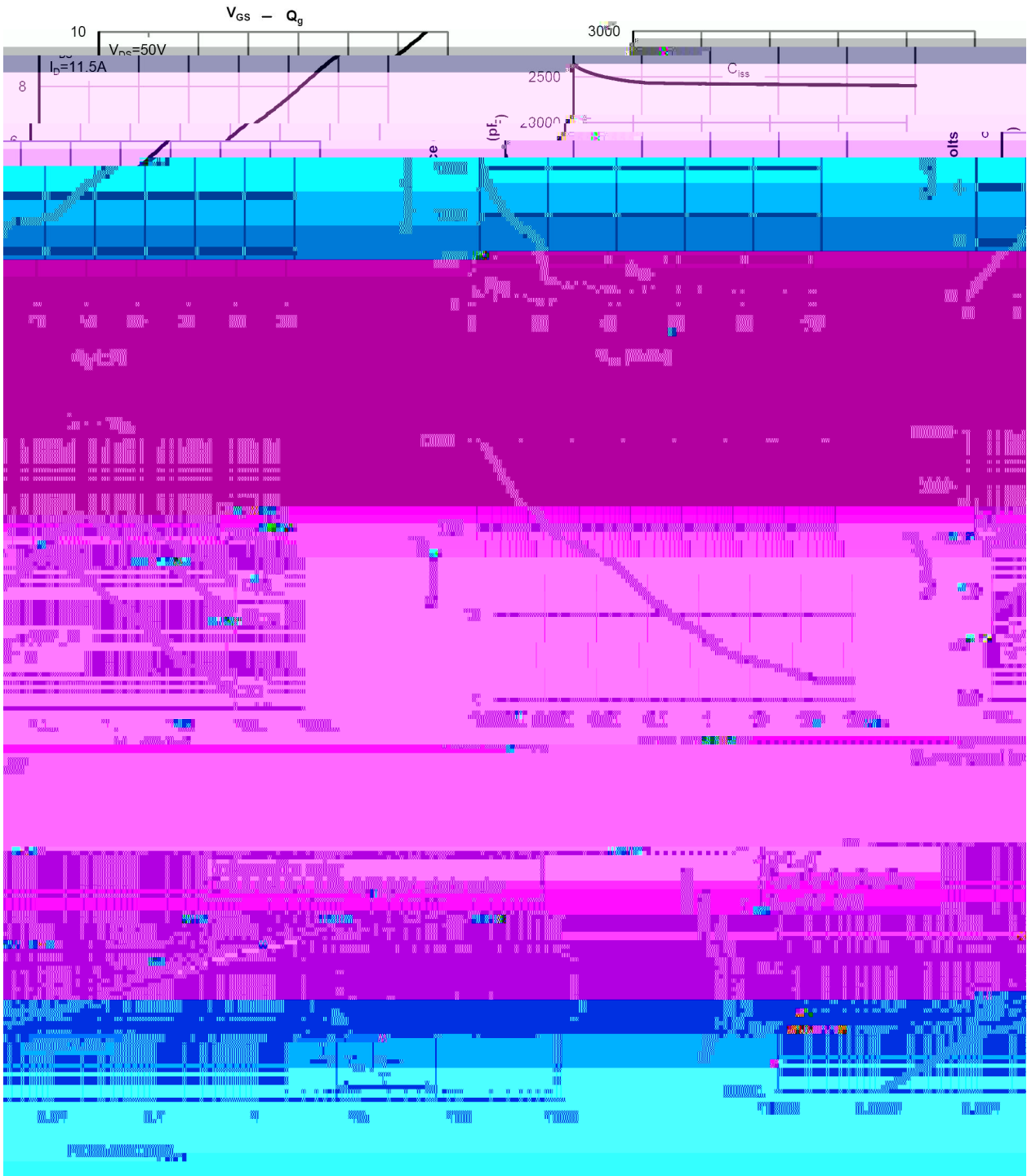
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_A=25$	$I_D$	11.5	A
	$T_A=70$		9.0	A

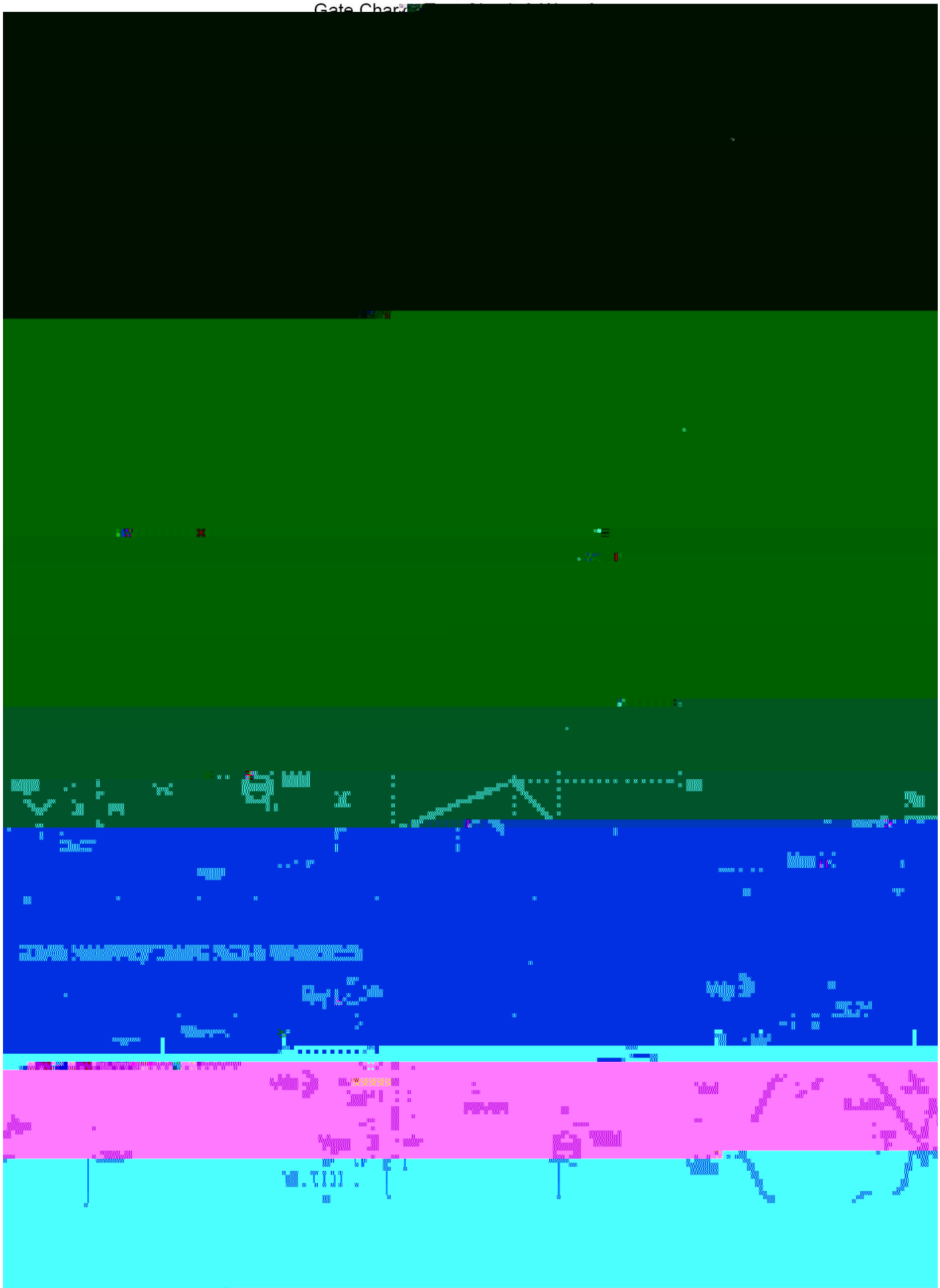
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Input Capacitance	$C_{iss}$	$V_{DS}=50V$ $V_{GS}=0V$ $f=1.0MHz$		2420		pF	
Output Capacitance	$C_{oss}$			170			
Reverse Transfer Capacitance	$C_{rss}$			11			
Gate resistance	$R_g$	$f=1.0MHz$	0.20	0.55	0.90		
Total Gate Charge(10V)	$Q_g$	$V_{DD}=10V$ $I_D=11.5A$ $V_{DS}=50V$		33	50	nC	
Total Gate Charge(4.5V)				15	25		
Gate-Source Charge			$Q_{gs}$		7.0		
Gate-Drain Charge			$Q_{gd}$		4.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V$ $V_{DS}=50V$ $R_L=4.35$ $R_{GEN}=3.0$		8.0		ns	
Turn-On Rise Time	$t_r$			3.0			
Turn-Off Delay Time	$t_{d(off)}$			25			
Turn-Off Fall Time	$t_f$			4.0			
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F=11.5A$ $di/dt=500A/\mu s$		25		ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$			110		nC	

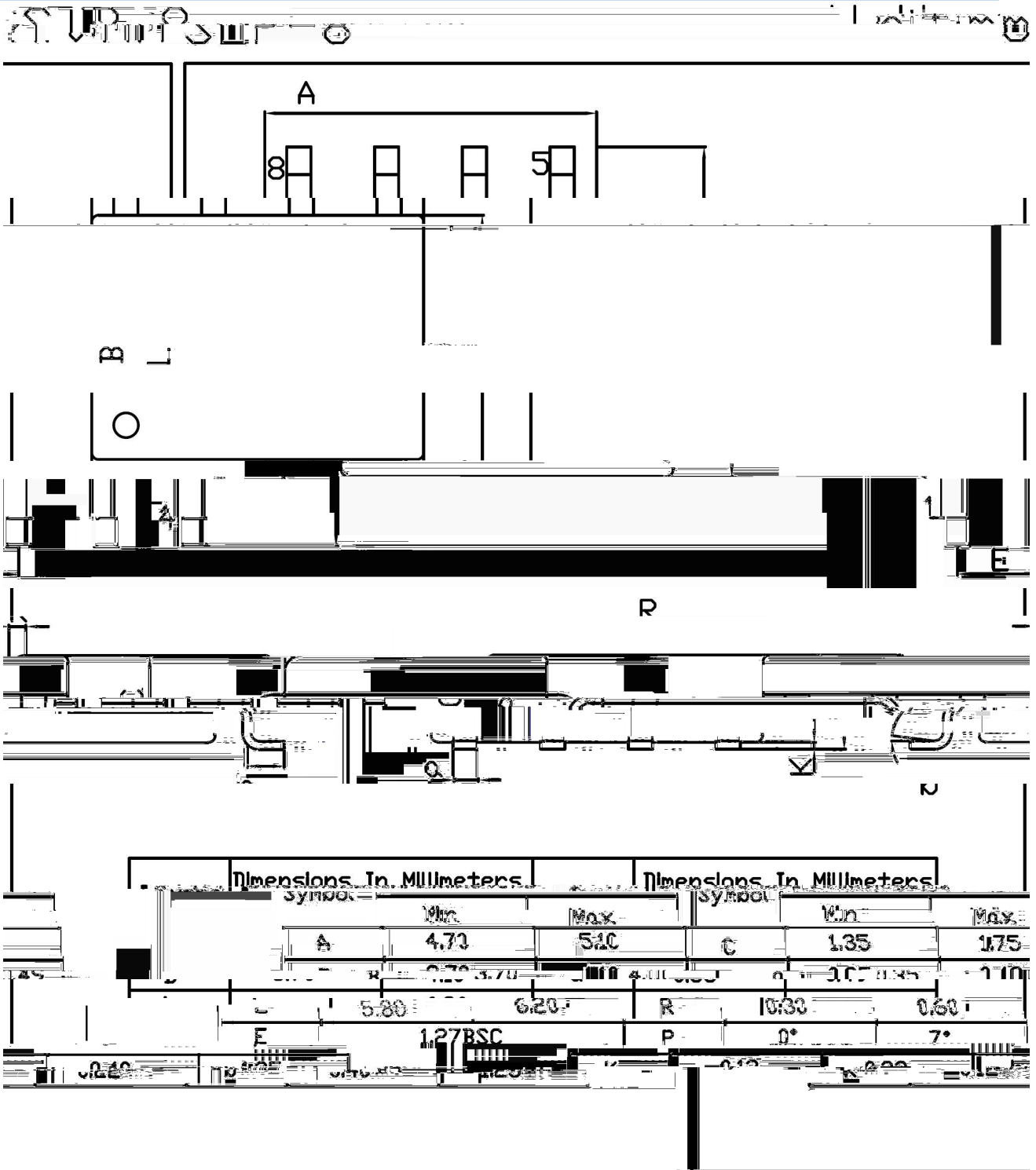
**Notes:**

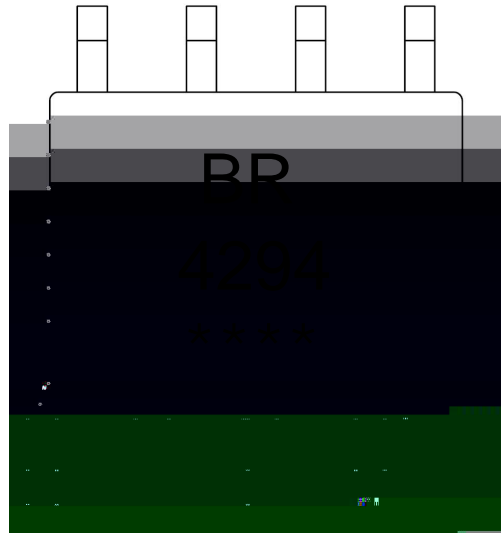
- A. The value of  $R_{JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ . The value in any given application depends on the user's specific board design.
- B. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^\circ C$ , using 10s junction-to-ambient thermal resistance.
- C. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ C$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J=25^\circ C$ .
- D. The  $R_{JA}$  is the sum of the thermal impedance from junction to lead  $R_{JL}$  and lead to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using  $<300\mu s$  pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of  $T_{J(MAX)}=150^\circ C$ . The SOA curve provides a single pulse rating.











BR

4294

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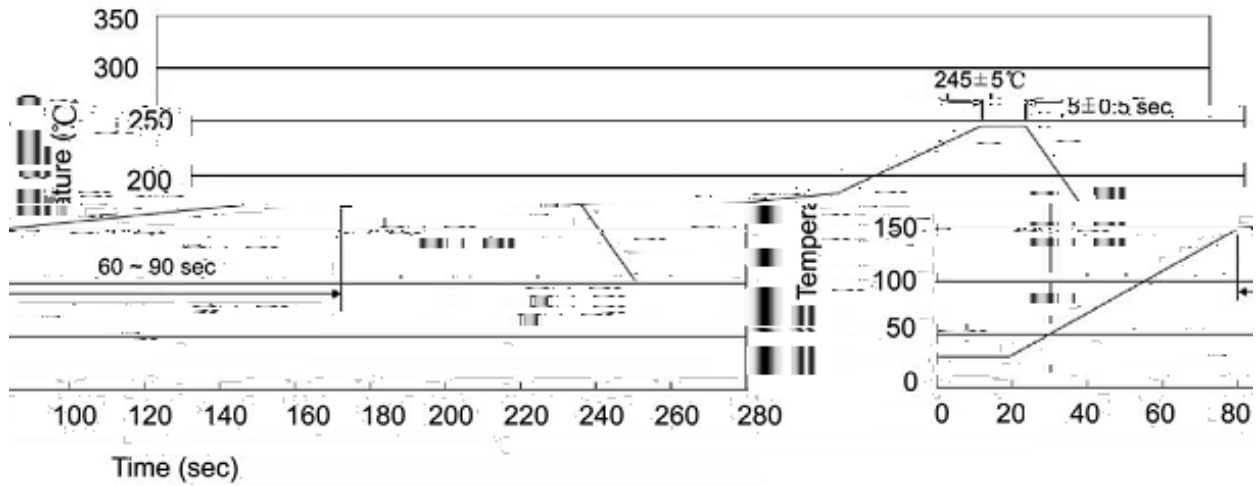
Note:

BR: Company Code.

4294 Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

### Temperature Profile for IR Reflow Soldering(Pb-Free)


**Note:**

- |   |       |     |    |           |  |
|---|-------|-----|----|-----------|--|
| 1 | 150   | 180 | 60 | 90sec;    | 1. Preheating: 150~180 , Time: 60~90sec.   |
| 2 | 245±5 |     |    | 5±0.5sec; | 2. Peak Temp.: 245±5 , Duration: 5±0.5sec. |
| 3 |       |     | 2  | 10 /sec.  | 3. Cooling Speed: 2~10 /sec.               |

260±5                      10±1 sec.                      Temp.: 260±5                      Time: 10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm <sup>3</sup> )		